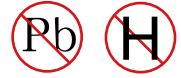




YEA SHIN TECHNOLOGY CO., LTD

YS3911S

P-Channel Enhancement MOSFET



VDS= -30V, ID= -4.1A

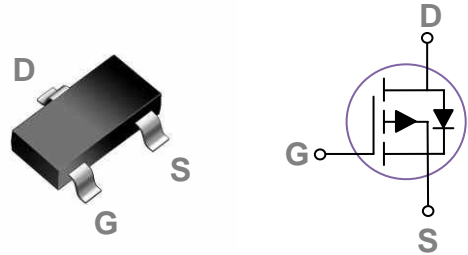
Features

- -30V,-4.1A, $R_{DS(ON)} = 55m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

SOT-23 Pin Configuration



Absolute Maximum Rating $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _A =25°C)	-4.1	A
	Drain Current – Continuous (T _A =70°C)	-3.3	A
I _{DM}	Drain Current – Pulsed ¹	-16.4	A
P _D	Power Dissipation (T _A =25°C)	1.56	W
	Power Dissipation – Derate above 25°C	0.012	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	80	°C/W

DEVICE CHARACTERISTICS

YS3911S

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-30V, V_{GS}=0V, T_J=25^\circ C$	---	---	-1	μA
		$V_{DS}=-24V, V_{GS}=0V, T_J=125^\circ C$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-source On-Resistance	$V_{GS}=-10V, I_D=-3A$	---	45	55	$m\Omega$
		$V_{GS}=-4.5V, I_D=-2A$	---	67	85	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.6	-2.2	V
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-3A$	---	3.5	---	S

Dynamic and Switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-3A$	---	5.1	7	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	2	3	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	2.2	4	
$T_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DD}=-15V, V_{GS}=-10V, R_G=6\Omega, I_D=-1A$	---	3.4	6	ns
T_r	Rise Time ^{2,3}		---	10.8	21	
$T_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	26.9	51	
T_f	Fall Time ^{2,3}		---	6.9	13	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$	---	560	810	pF
C_{oss}	Output Capacitance		---	55	80	
C_{rss}	Reverse Transfer Capacitance		---	40	60	

Drain-Source Diode Characteristics and Maximum Ratings

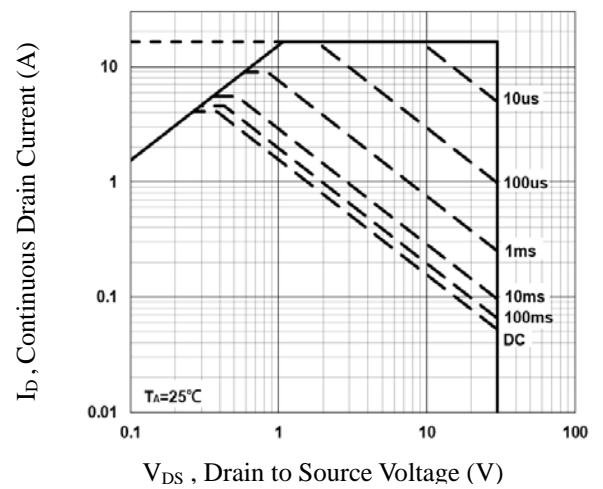
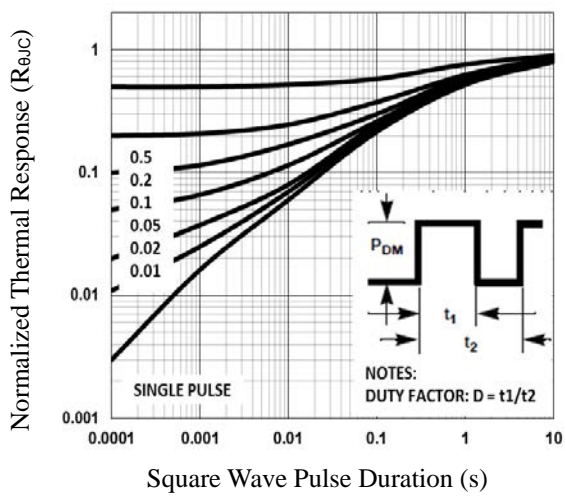
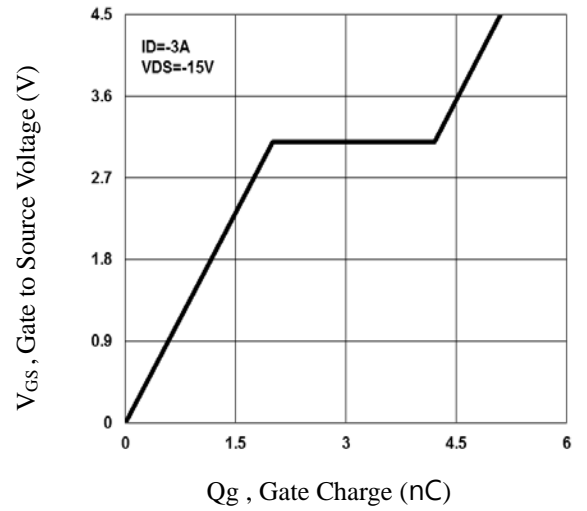
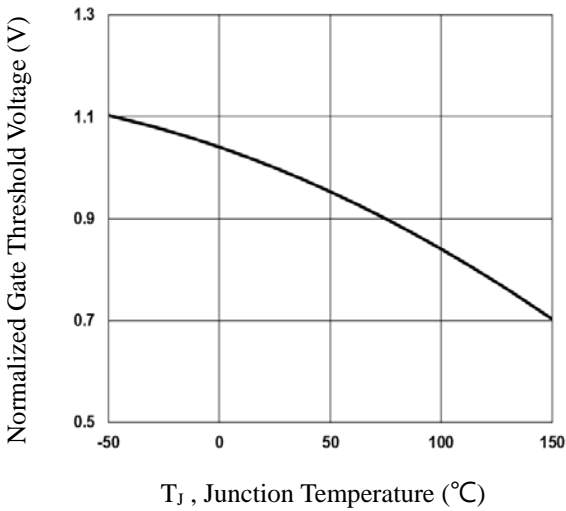
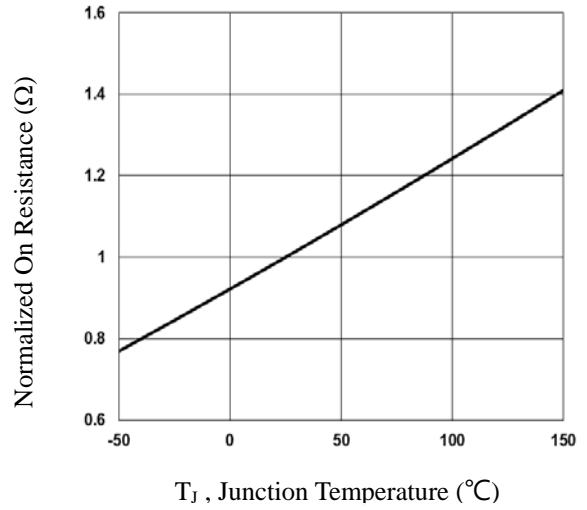
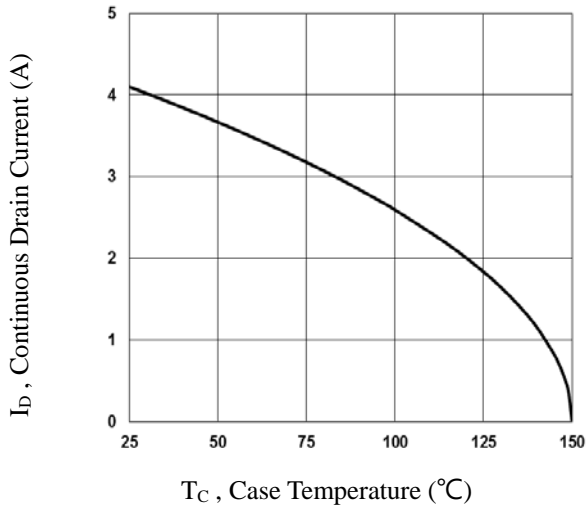
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-4.1	A
I_{SM}	Pulsed Source Current		---	---	-16.4	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ C$	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

DEVICE CHARACTERISTICS

YS3911S



DEVICE CHARACTERISTICS

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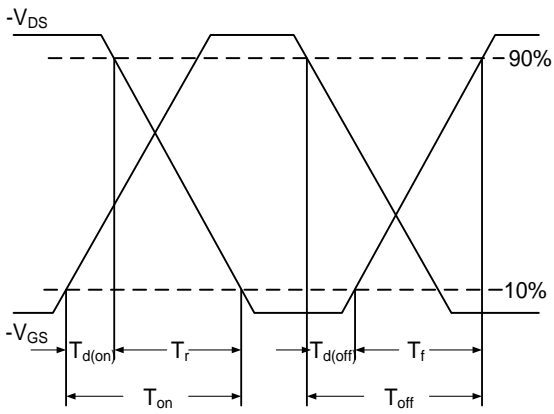


Fig.7 Switching Time Waveform

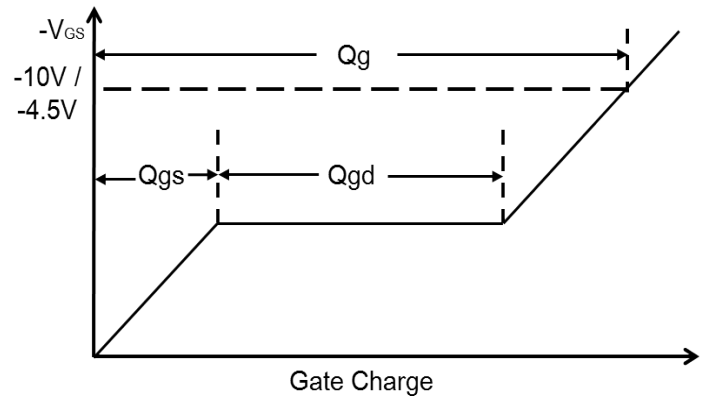
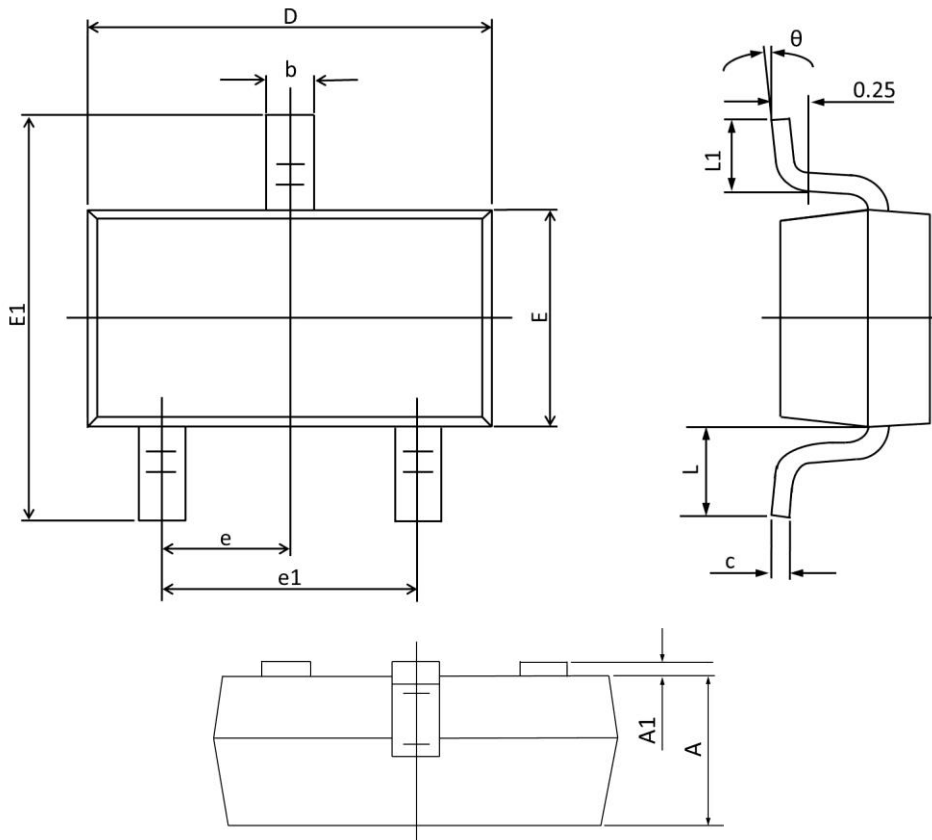


Fig.8 Gate Charge Waveform

PACKAGE OUTLINE & DIMENSIONS

YS3911S



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.000	0.035	0.039
A1	0.000	0.100	0.000	0.004
b	0.300	0.500	0.012	0.020
c	0.090	0.110	0.003	0.004
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	1°	7°	1°	7°